



DMN33D8LDWQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$3\Omega @ V_{GS} = 4.5V$	250mA
30V	5Ω @ V _{GS} = 4.0V	200mA
	7Ω @ V _{GS} = 2.5V	100mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- DC-DC Converters
- Backlighting

ESD PROTECTED



SOT363

Top View

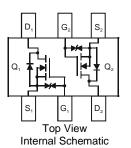
DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 5)

	Part Number	Case	Packaging					
	DMN33D8LDWQ-7	SOT363	3,000/Tape & Reel					
	DMN33D8LDWQ-13	SOT363	10,000/Tape & Reel					
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.							

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

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N33 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date	Code	Kev
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Year	201	9	2020		2021	20	22	2023		2024	4	2025
Code	G		Н		I		J	K		L		Μ
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Code												



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ State State T _A = +25°C T _A = +70°C		ID	250 200	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%))	I _{DM}	0.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P	0.35	w
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.22	vv
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	360	0CM/
Thermal Resistance, Junction to Case	R _{θJC}	126	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

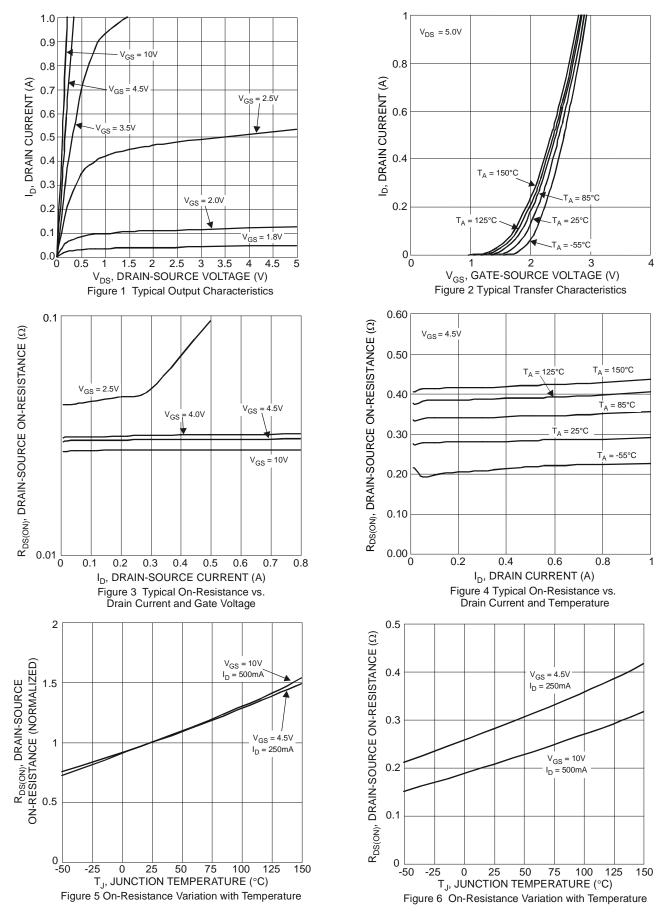
			-		-	-	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				-		. <u>.</u>	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current $@T_C = +25^{\circ}C$	IDSS		_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8		1.5	V	$V_{DS} = 3V, I_{D} = 100 \mu A$	
			_	2.4		$V_{GS} = 10V, I_D = 250mA$	
Static Drain-Source On-Resistance		_	_	3.0	Ω	$V_{GS} = 4.5V, I_D = 250mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	5.0	Ω	$V_{GS} = 4.0V, I_{D} = 10mA$	
		_	_	7.0		$V_{GS} = 2.5V, I_D = 5mA$	
Diode Forward Voltage	V _{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	Ciss	_	48	—	pF		
Output Capacitance	Coss	_	11	_	pF	V _{DS} = 5V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	8	_	pF		
Gate Resistance	Rg	_	57	—	Ω	f=1MHz, V _{GS} =0V, V _{DS} =0V	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	0.55	—	nC		
Total Gate Charge (V _{GS} = 10V)		_	1.23	_	nC)/ 10)/ L 050m A	
Gate-Source Charge	Q _{gs}	_	0.14	_	nC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q _{gd}	_	0.14	—	nC	1	
Turn-On Delay Time	t _{D(ON)}		2.9	—	ns		
Turn-On Rise Time	t _R		2.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}		18.2	—	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$	
Turn-Off Fall Time	t _F		13.6	—	ns	1	

Notes: 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

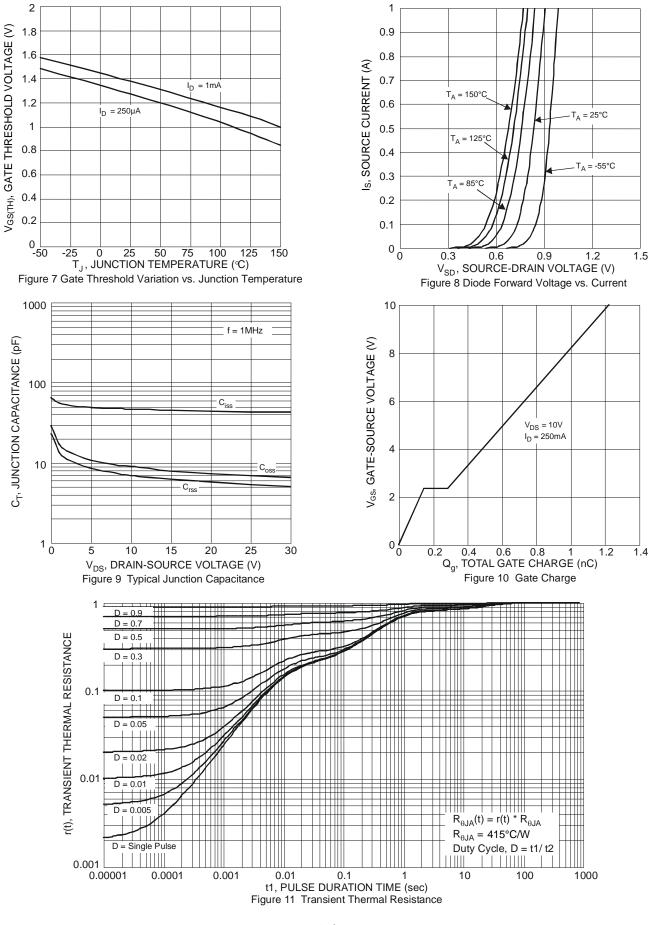


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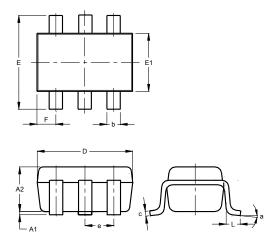
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Package Outline Dimensions

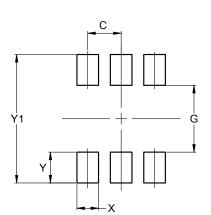
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363										
Dim	Min Max Typ									
A1	0.00	0.10	0.05							
A2	0.90 1.00 0.95									
b	0.10	0.30	0.25							
c	0.10	0.22	0.11							
D	1.80	2.20	2.15							
Е	2.00	2.20	2.10							
E1	1.15	1.30								
е	C).650 E	SC							
F	0.40	0.45	0.425							
_	0.25	0.40	0.30							
а	0°	8°								
All I	Dimen	sions	in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363

Dimensions	Value (in mm)
С	0.650
•	
G	1.300
Х	0.420
Y	0.600
Y1	2.500

SOT363



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